TSMC-02-262CIP

April 15, 2004

To: Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Fr: George O. Saile, Reg. No. 19,572
28 Davis Avenue
Poughkeepsie, N.Y. 12603

Subject: Serial No. 10/808,801 03/24/04

Tien-I Bao et al.

METHOD FOR FORMING OPENINGS IN LOW-K DIELECTRIC LAYERS

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation In An Application.

The following Patents and/or Publications are submitted to comply with the duty of disclosure under CFR 1.97-1.99 and 37 CFR 1.56.

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on April 26, 2004.

Stephen B. Ackerman, Reg. # 37761

Signature/Date 4/26/04

U.S. Patent 6,365,320 to Foote et al., "Process for Forming Anti-Reflective Film for Semiconductor Fabrication Using Extremely Short Wavelength Deep Ultraviolet Photo-lithography," discloses a process for an ARL.

U.S. Patent 6,376,392 to Lee et al., "PECVD Process for ULSI ARL," discloses a process for a ARL.

U.S. Patent 6,159,871 to Loboda et al., "Method for Producing Hydrogenated Silicon Oxycarbide Films Having Low Dielectric Constant," reveals a process for a H:SiOC layer.

U.S. Patent 5,926,740 to Forbes et al., "Graded Anti-Reflective Coating for IC Lithography," cited an amorphous silicon oxycarbide ARL formed either by high temperature pyrolysis of silicone resins, or by PECVD from silane, methane, and nitrous oxide precursors.

U.S. Patent 6,121,130 to Chua et al., "Laser Curing of Spin-On Dielectric Thin Films," discusses procedures for application and curing of methyl silsesquioxane low-k polymer films.

U.S. Patent 6,168,726 to Li et al., "Etching an Oxidized Organo-Silane Film," cites a number of oxygen free fluorocarbon etchants for Black Diamond and for HSQ.

U.S. Patent 6,372,661 to Lin et al., "Method to Improve the Crack Resistance of CVD Low-k Dielectric Constant Material," discusses a process using a ARL layers.

U.S. Patent 6,054,379 to Yau et al., "Method of Depositing a Low K Dielectric with Organo Silane," describes a CVD method.

U.S. Patent Application Publication US 2003/0134495 A1 to Gates et al., "Integration Scheme for Advanced BEOL Metallization Including Low-K Cap Layer and Method Thereof," discloses an advanced back-end-of-line (BEOL) metallization structure.

Sincerely,

Stephen B. Ackerman,
Reg. No. 37761

Form PTO-1449

INFORMATION DISCLOSURE CITATION IN AN APPLICATION

(Use several sheets if necessary)

Docket Number (Optional)	Application Number
TSMC-02-262CIP	10/808,801
Applicant	Tien-I. Bao et al.
Filing Date	Group Art Unit
03/24/04	

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	6365320	4/2/02	Foote et al.	430	270.1	1/19/99
	6376392	4/23/02	Lee et al.	438	778	5/18/01
	6159871	12/12/00	Loboda et al.	438	786	5/29/98
	5926740	7/20/99	Forbes et al.	438	763	10/27/97
	6121130	9/19/00	Chua et al.	438	623	11/16/98
	6168726	1/2/01	Li et al.	216	79	11/25/98
	6372661	4/16/02	Lin et al.	438	769	7/14/00
	6054379	4/25/00	Yau et al.	438	623	2/11/98

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation YES	Translation NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

– US. Patent App. Pub. US 2003/0134495 A1 to Gates et al., Pub. Date 07/17/03, Filed 01/15/02, U.S. Cl. 438/600.

EXAMINER	DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.